



UTT50P06-H

Preliminary

Power MOSFET

-35A, -60V P-CHANNEL (D-S) POWER MOSFET

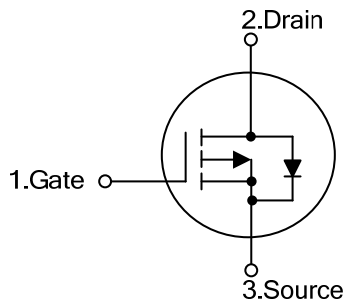
DESCRIPTION

The UTC **UTT50P06-H** is a P-channel power MOSFET using UTC's advanced technology to provide the customers with high switching speed and a minimum on-state resistance, and withstand high energy pulse in the avalanche and commutation mode. The UTC **UTT50P06-H** well suited for high efficiency fast switching applications.

FEATURES

- * $R_{DS(ON)} < 30m\Omega$ @ $V_{GS} = -10V$, $I_D = -8.0A$
- $R_{DS(ON)} < 40m\Omega$ @ $V_{GS} = -4.5V$, $I_D = -6.0A$
- * Fast switching
- * Green Device Available
- * Suit for -4.5V Gate Drive Applications

SYMBOL



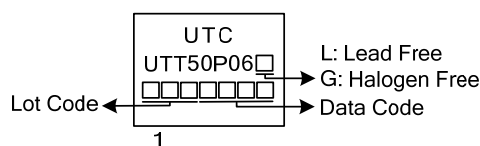
ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
UTT50P06L-TN3-R	UTT50P06G-TN3-R	TO-252	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>UTT50P06G-TN3-R</p> <p>(1) Packing Type</p> <p>(2) Package Type</p> <p>(3) Green Package</p>	<p>(1) R: Tape Reel</p> <p>(2) TN3: TO-252</p> <p>(3) G: Halogen Free and Lead Free, L: Lead Free</p>
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MARKING



■ ABSOLUTE MAXIMUM RATINGS ($T_C=25^\circ\text{C}$, unless otherwise specified)

PARAMETER			SYMBOL	RATINGS	UNIT
Drain-Source Voltage			V_{DSS}	-60	V
Gate-Source Voltage			V_{GSS}	± 20	V
Drain Current	Continuous	$T_C=25^\circ\text{C}$	I_D	-35	A
		$T_C=100^\circ\text{C}$		-22.1	A
	Pulsed		I_{DM}	-140	A
Power Dissipation			P_D	72.6	W
Junction Temperature			T_J	+150	$^\circ\text{C}$
Storage Temperature			T_{STG}	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

■ THERMAL CHARACTERISTICS

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient		θ_{JA}	62	$^\circ\text{C/W}$
Junction to Case		θ_{JC}	1.72	$^\circ\text{C/W}$

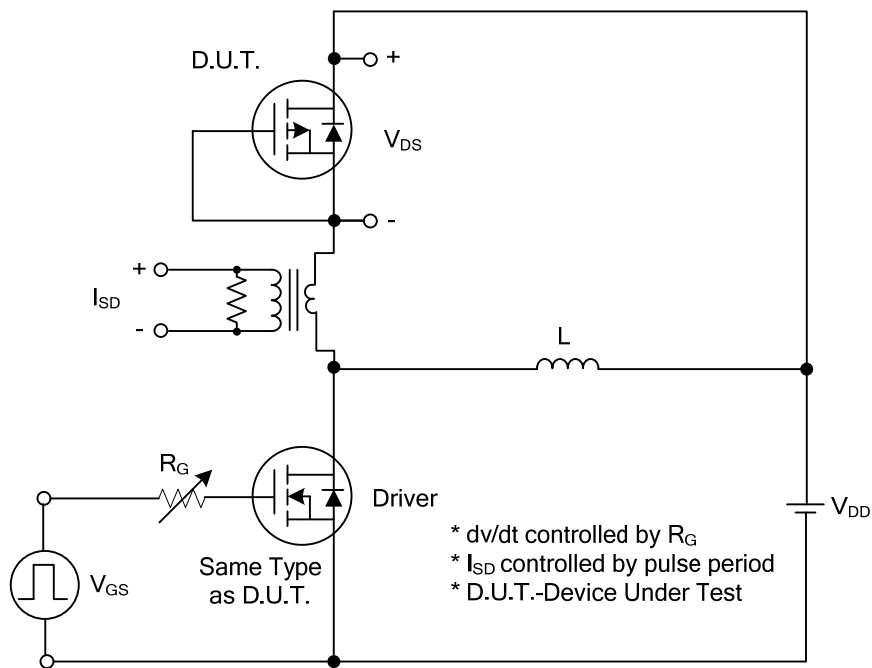
■ ELECTRICAL CHARACTERISTICS ($T_J=25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV _{DSS}	V _{GS} =0 V, I _D =-250μA	-60			V
Drain-Source Leakage Current		I _{DSS}	V _{DS} =-60V, V _{GS} =0V			-1	μA
			V _{DS} =-48V, V _{GS} =0V, T _J =125°C			-10	μA
Gate-Source Leakage Current	Forward	I _{GSS}	V _{GS} =+20V, V _{DS} =0V			100	nA
	Reverse		V _{GS} =-20V, V _{DS} =0V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		V _{GS(TH)}	V _{DS} =V _{GS} , I _D =-250μA	-1.0		-2.5	V
Static Drain-Source On-Resistance		R _{DS(ON)}	V _{GS} =-10V, I _D =-8.0A			30	mΩ
			V _{GS} =-4.5V, I _D =-6.0A			40	mΩ
DYNAMIC PARAMETERS							
Input Capacitance		C _{ISS}	V _{DS} =-25V, V _{GS} =0V, f=1.0MHz		2595	3900	pF
Output Capacitance		C _{OSS}			162	240	pF
Reverse Transfer Capacitance		C _{RSS}			115	170	pF
SWITCHING PARAMETERS (Note 1, 2)							
Total Gate Charge		Q _G	V _{DS} =-30V, V _{GS} =-10V, I _D =-5.0A		43.8	88	nC
Gate Source Charge		Q _{GS}			4.6	9	nC
Gate Drain Charge		Q _{GD}			8.3	17	nC
Turn-ON Delay Time		t _{D(ON)}	V _{DD} =-30V, V _{GS} =-10V, I _D =-1.0A, R _G =6.0Ω		25	50	ns
Turn-ON Rise Time		t _R			13.8	28	ns
Turn-OFF Delay Time		t _{D(OFF)}			148	29	ns
Turn-OFF Fall-Time		t _F			51	100	ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Body-Diode Continuous Current		I _S				-35	A
Maximum Pulsed Drain-Source Diode Forward Current		I _{SM}				-70	A
Diode Forward Voltage		V _{SD}	I _S =-1.0A, V _{GS} =0V			-1	V

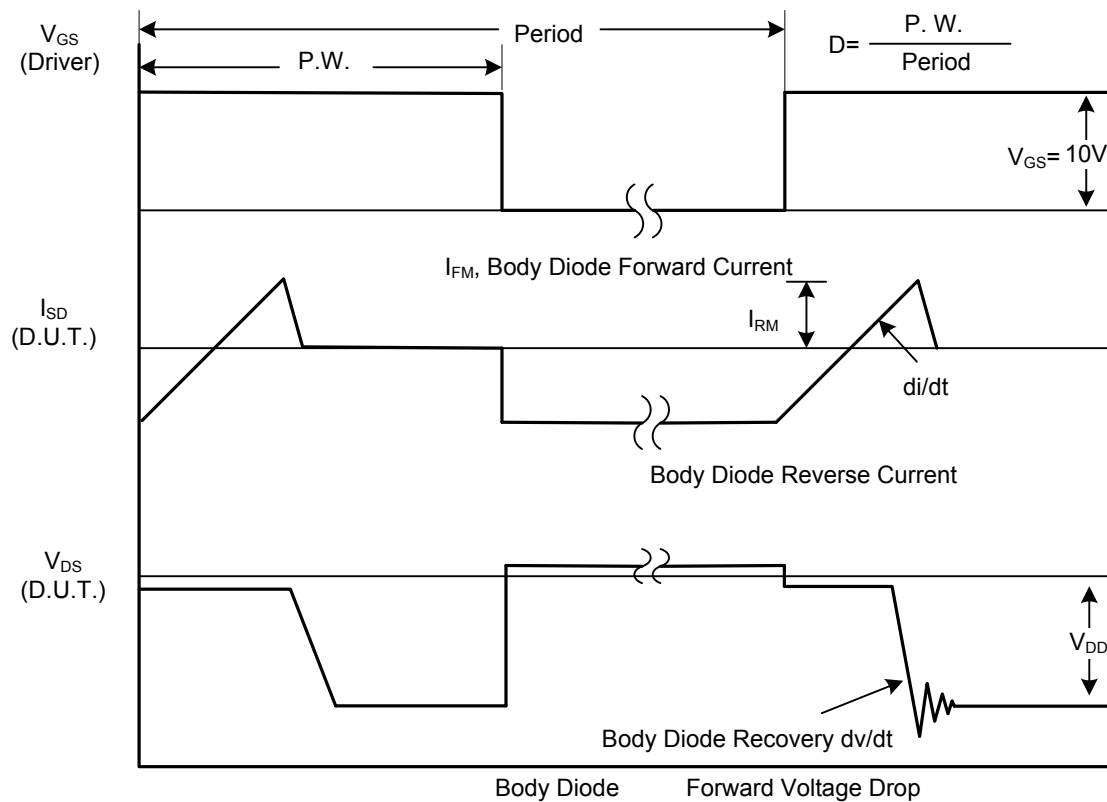
Notes: 1. Pulse Test : Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$.

2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

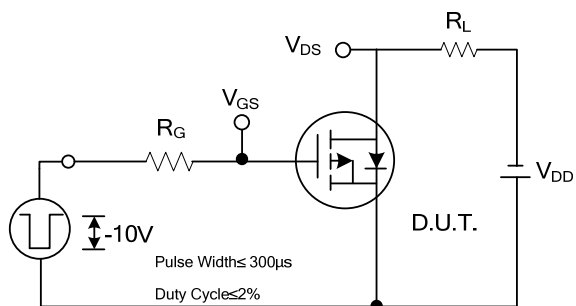


Peak Diode Recovery dv/dt Test Circuit

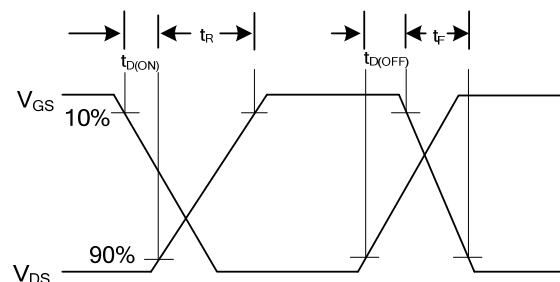


Peak Diode Recovery dv/dt Waveforms

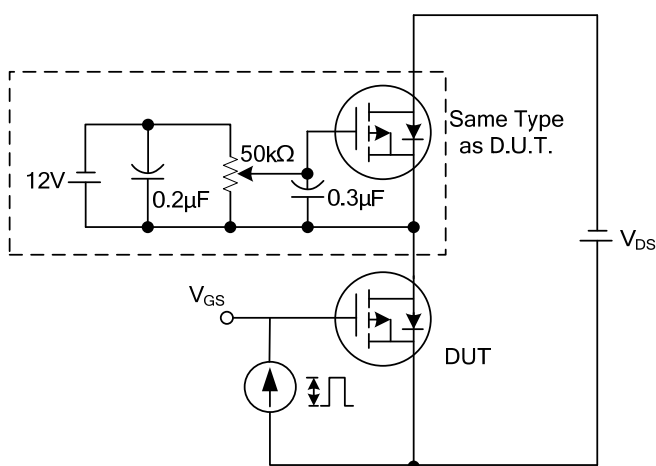
■ TEST CIRCUITS AND WAVEFORMS (Cont.)



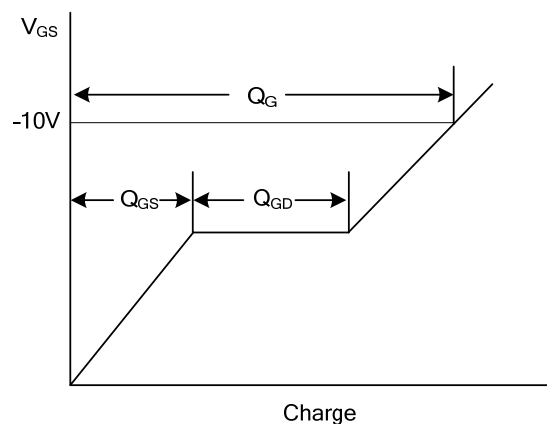
Switching Test Circuit



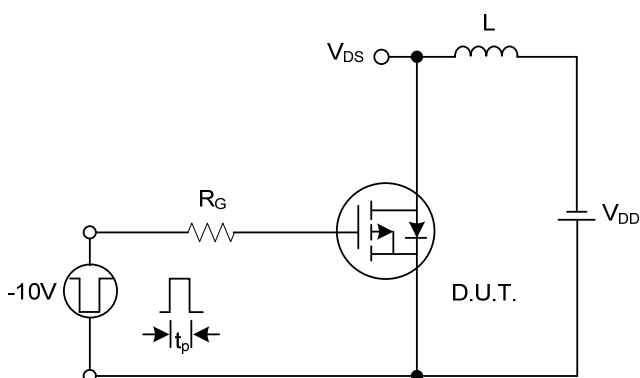
Switching Waveforms



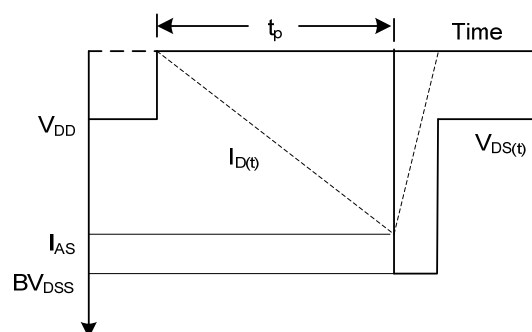
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

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